CHP-412 Materials Chemistry and Catalysis

Item Text	Option Text 1	Option Text 2	Option Text 3	Option Text 4
The general Staichiametric formulaof perovskites is	AB2X3	ABX3	ABX2	ABX4
Langmuir - Bladgett film technique has organized monolayer of	Amphoteric molecules from air-water interface	Amphiphilic molecules from air- oil interface	Amphiphilic molecules from air- water interface	Amphoteric molecules from air-oil interface
The most correct statement for full wave rectifier (During positive input cycle) is	Diode (D1) forward biased and Diode (D2) reversed biased	Diode (D1) reversed biased and Diode (D2) forward biased	Diode (D1) Diode (D2) both forward biased	Diode (D1) Diode (D2) both reversed biased
Perovskite structure has	SCP	BBC	FCC	НСР
Which of the following solvent is used in langmuir- Blodgettfilm technique?	Water insoluble volatile solvent	Water soluble volatile solvent	Water insoluble nonvolatile solvent	Water soluble nonvolatile solvent
Which of the following is a sputtering gas?	Hydrogen	Nitrogen	Oxygen	Argon
Ripple factor of full wave and half wave respectively ?	High & Low	Low & High	Low & Low	High & High
Which of the following operation, transistor act as an amplifier ?	Saturated mode of operation	Cutoff mode of operation	Active mode of operation	Super Saturated mode of operation
Which of the following is not a family of superconducting cuprates ?	LSCO	YBCO	BSCCO	LBCO
the 2-1-4 material is nothing but	LCO	YBCO	LBCO	BSCCO
The crystals of 1-2-3 material having oxygen content greater and crytical value is ————	Cubic in nature	Tetragonal in nature	Orthorhombic in nature	Hexagonal in nature

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In case of active mode of operation collector based junction and emiter based junction respectiely	Forward biased and reverse biased	Reversed biased and forward biased	Both are forward biased	Bothe are reverse biased
The capacitance value of capacitor is	10 pF to 1 nF	1 nF to 1 uF	1uF to 1 mF	1mF to 1 kF
In the RF Sputtering , target is	Metal	Semiconductor	Insulator	Metalloid
Metal Organic Chemical Vapor Deposition (MOCVD) has	Deposition of Semiconductor	Deposition of metal	Deposition of Insulator	Deposition of Metalloid
In Photolithogrphy technique photoresist material will polymerize if exposed to	IR Radiation	Microwave radiation	UV Radiation	Visible Radiation
The dielectric material used in capacitor is	Semiconductor	Metal	Superconductor	Insulator
In preparation of 1-2-3 material the critical value of oxygen content (Y) is	6.35	6.25	7.25	7.35
Incase of LSCO Superconducting Cuprates 'S' indicates :	Sulphur	Selenium	Silicone	Strontium
Anisotropy implies different propertiesin :	All direction	Single direction	Not dependent of direction	only 2 directions